Session Title: 42. Oxide TFT IV

Session Date: August 25 (Fri.), 2023

Session Time: 09:00-10:30

Session Room: Room B (214~215)

Session Chair(s): Prof. Takashi Noguchi (Univ. of the Ryukyus, Japan)
Prof. Hyun Suk Kim (Chungnam Nat'l Univ., Korea)

[B42-1] [Invited] 09:00-09:25

Material Design and Strategies for Thermally Stable Oxide Semiconductor toward Three-Dimensional Integrated Device Application

Takanori Takahashi and Yukiharu Uraoka (Nara Inst. of Science and Tech., Japan)

[B42-2] 09:25-09:40

Indium Gallium Zinc Oxide Phototransistor with Porous Silica Layer for Visible Light Detection

Jae Seong Han, Kyungmoon Kwak, Kyungho Park, Jong Bin An, Youjin Seo, and Hyun Jae Kim (Yonsei Univ., Korea)

[B42-3] [Invited] 09:40-10:05

Analysis of Defect / Interface States for Oxide TFTs Utilizing HAX-PES

Junghwan Kim, Xuejian Zhang (UNIST, Korea), Kihyung Sim (Tokyo Inst. of Tech., Japan), Hyun-woo Park (LG Display Co. Ltd., Korea), Kwun-Bum Chung (Dongguk Univ., Korea), and Hideo Hosono (Tokyo Inst. of Tech., Japan)

[B42-4] [Invited] 10:05-10:30

All-Sputter-Deposited $Hf_{0.5}Zr_{0.5}O_2$ Double-Gate Ferroelectric Thin-Film Transistor with Amorphous Indium-Gallium-Zinc Oxide Channel

Soi Jeong (Inha Univ., Korea), Changhyeon Han, and Daewoong Kwon (Hanyang Univ., Korea)